HEF4049B

Hex inverting buffers

Rev. 08 — 2 December 2009

Product data sheet

1. General description

The HEF4049B provides six inverting buffers with high current output capability suitable for driving TTL or high capacitive loads. Since input voltages in excess of the buffers' supply voltage are permitted, the buffers may also be used to convert logic levels of up to 15 V to standard TTL levels. Their guaranteed fan-out into common bipolar logic elements is shown in Table 3.

It operates over a recommended V_{DD} power supply range of 3 V to 15 V referenced to V_{SS} (usually ground). Unused inputs must be connected to V_{DD} , V_{SS} , or another input. It is also suitable for use over the industrial (–40 °C to +85 °C) temperature range.

2. Features

- Accepts input voltages in excess of the supply voltage
- Fully static operation
- 5 V, 10 V, and 15 V parametric ratings
- Standardized symmetrical output characteristics
- Operates across the full industrial temperature range –40 °C to +85 °C
- Complies with JEDEC standard JESD 13-B

3. Applications

- Industrial
- LOCMOS (Local Oxidation CMOS) to DTL/TTL converter
- HIGH sink current for driving two TTL loads
- HIGH-to-LOW level logic conversion

4. Ordering information

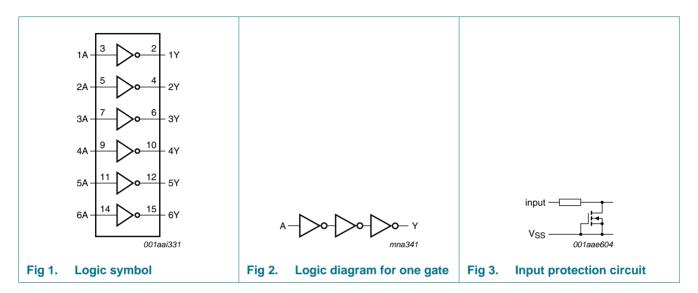
Table 1. Ordering information

All types operate from -40 °C to +85 °C.

Type number	Package					
	Name	Description	Version			
HEF4049BP	DIP16	plastic dual in-line package; 16 leads (300 mil)	SOT38-4			
HEF4049BT	SO16	plastic small outline package; 16 leads; body width 3.9 mm	SOT109-1			

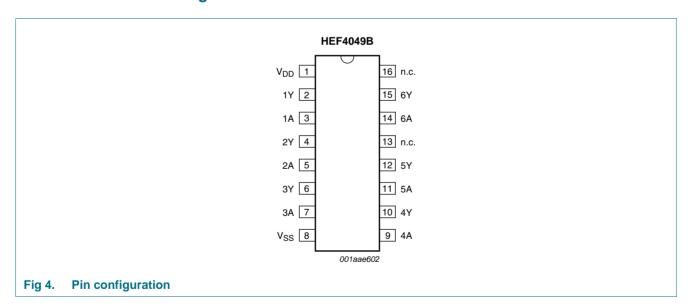


5. Functional diagram



6. Pinning information

6.1 Pinning



6.2 Pin description

Table 2. Pin description

Symbol	Pin	Description
V_{DD}	1	supply voltage
1Y to 6Y	2, 4, 6, 10, 12, 15	output

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Table 2. Pin description ...continued

Symbol	Pin	Description
1A to 6A	3, 5, 7, 9, 11, 14	input
V _{SS}	8	ground supply voltage
n.c.	13, 16	not connected

7. Functional description

Table 3. Guaranteed fan-out

Driven element	Guaranteed fan-out
Standard TTL	2
74 LS	9
74 L	16

8. Limiting values

Table 4. Limiting values

In accordance with the Absolute Maximum Rating System (IEC 60134).

Symbol	Parameter	Conditions	Min	Max	Unit
V_{DD}	supply voltage		-0.5	+18	V
I _{IK}	input clamping current	$V_I < -0.5 \text{ V or } V_I > V_{DD} + 0.5 \text{ V}$	-	±10	mA
VI	input voltage		-0.5	$V_{DD} + 0.5$	V
I _{OK}	output clamping current	$V_O < -0.5 \text{ V or } V_O > V_{DD} + 0.5 \text{ V}$	-	±10	mA
I _{I/O}	input/output current		-	±10	mA
I _{DD}	supply current		-	50	mA
T _{stg}	storage temperature		-65	+150	°C
T _{amb}	ambient temperature		-40	+85	°C
P _{tot}	total power dissipation	T_{amb} -40 °C to +85 °C			
		DIP16 package	<u>[1]</u> -	750	mW
		SO16 package	[2] -	500	mW
Р	power dissipation	per output	-	100	mW

^[1] For DIP16 package: P_{tot} derates linearly with 12 mW/K above 70 °C.

9. Recommended operating conditions

Table 5. Recommended operating conditions

Symbol	Parameter	Conditions	Min	Тур	Max	Unit
V_{DD}	supply voltage		3	-	15	V
V_{I}	input voltage		0	-	V_{DD}	V
T _{amb}	ambient temperature	in free air	-40	-	+85	°C

^[2] For SO16 package: P_{tot} derates linearly with 8 mW/K above 70 °C.

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 Table 5.
 Recommended operating conditions ...continued

Symbol	Parameter	Conditions	Min	Тур	Max	Unit
$\Delta t/\Delta V$	input transition rise and fall rate	$V_{DD} = 5 V$	-	-	3.75	μs/V
		V _{DD} = 10 V	-	-	0.5	μs/V
		V _{DD} = 15 V	-	-	0.08	μs/V

10. Static characteristics

Table 6. Static characteristics

 $V_{SS} = 0$ V; $V_I = V_{SS}$ or V_{DD} unless otherwise specified.

Parameter	Conditions	iditions V _{DD}	T _{amb} =	T _{amb} = -40 °C		T _{amb} = 25 °C		T _{amb} = 85 °C	
			Min	Max	Min	Max	Min	Max	
HIGH-level input voltage	$ I_{O} < 1 \mu A$	5 V	3.5	-	3.5	-	3.5	-	V
		10 V	7.0	-	7.0	-	7.0	-	V
		15 V	11.0	-	11.0	-	11.0	-	V
LOW-level input voltage	$ I_{O} < 1 \mu A$	5 V	-	1.5	-	1.5	-	1.5	V
		10 V	-	3.0	-	3.0	-	3.0	V
		15 V	-	4.0	-	4.0	-	4.0	V
HIGH-level output voltage	$ I_{O} < 1 \mu A$	5 V	4.95	-	4.95	-	4.95	-	V
		10 V	9.95	-	9.95	-	9.95	-	V
		15 V	14.95	-	14.95	-	14.95	-	V
LOW-level output voltage	$ I_{O} < 1 \mu A$	5 V	-	0.05	-	0.05	-	0.05	V
		10 V	-	0.05	-	0.05	-	0.05	V
		15 V	-	0.05	-	0.05	-	0.05	V
HIGH-level output current	$V_0 = 2.5 \text{ V}$	5 V	-1.7	-	-1.4	-	-1.1	-	mΑ
	$V_0 = 4.6 \text{ V}$	5 V	-0.52	-	-0.44	-	-0.36	-	mΑ
	$V_0 = 9.5 \ V$	10 V	-1.3	-	-1.1	-	-0.9	-	mΑ
	$V_0 = 13.5 \text{ V}$	15 V	-3.6	-	-3.0	-	-2.4	-	mΑ
LOW-level output current	$V_0 = 0.4 \ V$	4.75 V	3.5	-	2.9	-	2.3	-	mΑ
	$V_0 = 0.5 \ V$	10 V	12.0	-	10.0	-	8.0	-	mΑ
	$V_0 = 1.5 \text{ V}$	15 V	24.0	-	20.0	-	16.0	-	mΑ
input leakage current	$V_{DD} = 15 \text{ V}$	15 V	-	±0.3	-	±0.3	-	±1.0	μΑ
supply current	$I_O = 0 A$	5 V	-	4.0	-	4.0	-	30	μΑ
		10 V	-	8.0	-	8.0	-	60	μΑ
		15 V	-	16.0	-	16.0	-	120	μΑ
input capacitance			-	-	-	7.5	-	-	pF
	HIGH-level input voltage LOW-level input voltage HIGH-level output voltage LOW-level output voltage HIGH-level output current LOW-level output current input leakage current supply current	HIGH-level input voltage $ I_O < 1 \mu A$ LOW-level input voltage $ I_O < 1 \mu A$ HIGH-level output voltage $ I_O < 1 \mu A$ LOW-level output voltage $ I_O < 1 \mu A$ HIGH-level output current $V_O = 2.5 V$ $V_O = 4.6 V$ $V_O = 9.5 V$ $V_O = 13.5 V$ LOW-level output current $V_O = 0.4 V$ $V_O = 0.5 V$ $V_O = 1.5 V$ input leakage current $V_{DD} = 15 V$ supply current $V_O = 0.4 V$	HIGH-level input voltage $ I_O < 1 \ \mu A$ $5 \ V$ $10 \ V$ $15 \ V$ $10 \$	$ \begin{tabular}{ c c c c c c c c c c c c c c c c c c c$	$\begin{tabular}{ c c c c c c c c c c c c c c c c c c c$	$\begin{tabular}{ c c c c c c c c c c c c c c c c c c c$	HIGH-level input voltage HIGH-level output current		HIGH-level input voltage Hole 1 μA 1 μ

11. Dynamic characteristics

Table 7. Dynamic characteristics

 $V_{SS} = 0 \text{ V; } C_L = 50 \text{ pF; } t_f = t_f \le 20 \text{ ns; } T_{amb} = 25 \text{ °C; } unless \text{ otherwise specified.}$

Symbol	Parameter	Conditions	V_{DD}	Extrapolation formula	Min	Тур	Max	Unit
t_{PHL}	HIGH to LOW	HIGH to LOW nA to nY;	5 V [1]	26 ns + $(0.18 \text{ ns/pF})C_L$	-	35	70	ns
	propagation delay	see Figure 5	10 V	11 ns + (0.08 ns/pF)C _L	-	15	30	ns
			15 V	9 ns + $(0.05 \text{ ns/pF})C_L$	-	12	25	ns
t _{PLH}	LOW to HIGH	nA to nY;	5 V [1]	23 ns + $(0.55 \text{ ns/pF})C_L$	-	50	100	ns
	propagation delay see Figure 5	10 V	14 ns + (0.23 ns/pF)C _L	-	25	50	ns	
			15 V	12 ns + (0.16 ns/pF)C _L	-	20	40	ns
t_{THL}	HIGH to LOW output stransition time	ransition time	5 V [1]	3 ns + $(0.35 \text{ ns/pF})C_L$	-	20	40	ns
			10 V	$3 \text{ ns} + (0.14 \text{ ns/pF})C_L$	-	10	20	ns
			15 V	2 ns + $(0.09 \text{ ns/pF})C_L$	-	7	14	ns
t_{TLH}	LOW to HIGH output	naition time	5 V [1]	10 ns + $(1.00 \text{ ns/pF})C_L$	-	60	120	ns
	transition time		10 V	9 ns + (0.42 ns/pF)C _L	-	30	60	ns
			15 V	6 ns + (0.28 ns/pF)C _L	-	20	40	ns

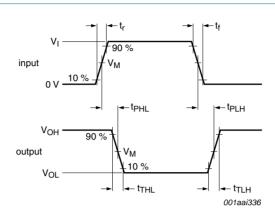
^[1] The typical values of the propagation delay and transition times are calculated from the extrapolation formulas shown (C_L in pF).

Table 8. Dynamic power dissipation P_D

 P_D can be calculated from the formulas shown. $V_{SS} = 0$ V; $t_r = t_f \le 20$ ns; $T_{amb} = 25$ °C.

Symbol	Parameter	V_{DD}	Typical formula for P _D (μW)	where:
P_D	dynamic power	5 V	$P_D = 2500 \times f_i + \Sigma (f_o \times C_L) \times V_{DD}^2$	f_i = input frequency in MHz;
	dissipation	10 V	$P_D = 11000 \times f_i + \Sigma (f_o \times C_L) \times V_{DD}^2$	fo = output frequency in MHz;
		15 V	$P_D = 35000 \times f_i + \Sigma (f_o \times C_L) \times V_{DD}^2$	C _L = output load capacitance in pF;
				V_{DD} = supply voltage in V;
				$\Sigma(f_o \times C_L)$ = sum of the outputs.

12. Waveforms



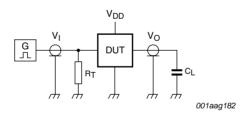
Measurement points are given in Table 9.

 V_{OL} and V_{OH} are typical output voltage levels that occur with the output load.

Fig 5. Input (nA) to output (nY) propagation delays and transition times

Table 9. Measurement points

Input		Output			
V _M	VI	V _M	V _X	V _Y	
0.5V _{DD}	0 V to V _{DD}	0.5V _{DD}	0.1V _{DD}	0.9V _{DD}	



Test data is given in Table 10.

Definitions for test circuit:

 C_L = Load capacitance including jig and probe capacitance.

 R_T = Termination resistance should be equal to output impedance Z_o of the pulse generator.

Fig 6. Load circuitry for switching times

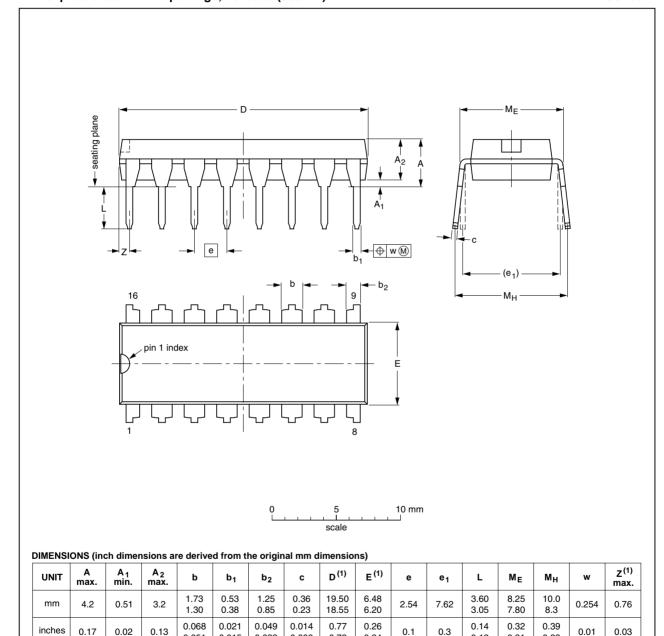
Table 10. Test data

Supply voltage	Input	Load		
	VI	V _M	t _r , t _f	C _L
5 V to 15 V	V_{DD}	0.5V _I	≤ 20 ns	50 pF

13. Package outline

DIP16: plastic dual in-line package; 16 leads (300 mil)

SOT38-4



Note

0.015

0.033

0.009

0.051

OUTLINE		REFER	EUROPEAN	ICCUE DATE		
VERSION	IEC	JEDEC	JEITA		PROJECTION	ISSUE DATE
SOT38-4						95-01-14 03-02-13

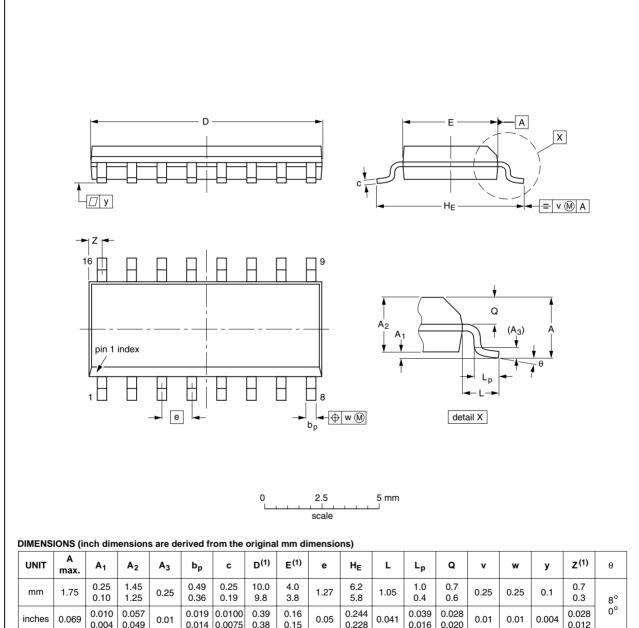
Fig 7. Package outline SOT38-4 (DIP16)

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^{1.} Plastic or metal protrusions of 0.25 mm (0.01 inch) maximum per side are not included.

SO16: plastic small outline package; 16 leads; body width 3.9 mm

SOT109-1



ι	JNIT	A max.	A ₁	A ₂	A ₃	bp	С	D ⁽¹⁾	E ⁽¹⁾	е	HE	L	Lp	Q	v	w	у	Z ⁽¹⁾	θ
	mm	1.75	0.25 0.10	1.45 1.25	0.25	0.49 0.36	0.25 0.19	10.0 9.8	4.0 3.8	1.27	6.2 5.8	1.05	1.0 0.4	0.7 0.6	0.25	0.25	0.1	0.7 0.3	8°
in	ches	0.069	0.010 0.004	0.057 0.049	0.01		0.0100 0.0075		0.16 0.15	0.05	0.244 0.228	0.041	0.039 0.016	0.028 0.020	0.01	0.01	0.004	0.028 0.012	0°

Note

1. Plastic or metal protrusions of 0.15 mm (0.006 inch) maximum per side are not included.

OUTLINE		REFER	EUROPEAN	ISSUE DATE		
VERSION	IEC	JEDEC	JEITA		PROJECTION	ISSUE DATE
SOT109-1	076E07	MS-012				99-12-27 03-02-19

Fig 8. Package outline SOT109-1 (SO16)

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14. Abbreviations

Table 11. Abbreviations

Acronym	Description
DTL	Diode Transistor Logic
LOCMOS	Local Oxidation CMOS
TTL	Transistor Transistor Logic

15. Revision history

Table 12. Revision history

Product data sheet

Document ID	Release date	Data sheet status	Change notice	Supersedes
HEF4049B_8	20091202	Product data sheet	-	HEF4049B_7
Modifications:	Section 8 "I	<u>imiting values"</u> ∆t/∆V value	s updated.	
HEF4049B_7	20090721	Product data sheet	-	HEF4049B_6
HEF4049B_6	20090325	Product data sheet	-	HEF4049B_5
HEF4049B_5	20081111	Product data sheet	-	HEF4049B_4
HEF4049B_4	20080704	Product data sheet	-	HEF4049B_CNV_3
HEF4049B_CNV_3	19950101	Product specification	-	HEF4049B_CNV_2
HEF4049B_CNV_2	19950101	Product specification	-	-

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Preliminary [short] data sheet	Qualification	This document contains data from the preliminary specification.
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